MOS FET

#### FL6L52010L

# **Panasonic**

### FL6L52010L

Silicon P-channel MOSFET(FET) Silicon epitaxial planar type(SBD)

For switching For DC-DC Converter

#### ■ Features

- Low drain-source ON resistance : RDS (on) typ. = 80 m $\Omega$  ( VGS = -4.0 V )
- Low drive voltage : 1.8 V drive
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL:Level 1 compliant)

■ Marking Symbol : Y1

Established: 2010-09-17

: 2013-10-17

Revised

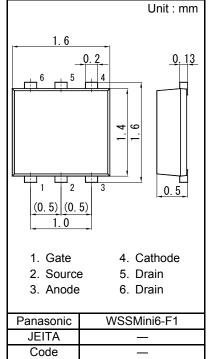
#### ■ Packaging

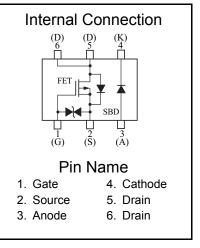
Embossed type (Thermo-compression sealing) 10 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

| 項目      |                               | Symbol | Rating      | Unit |  |
|---------|-------------------------------|--------|-------------|------|--|
| FET     | Drain to Source Voltage       | VDS    | -20         | V    |  |
|         | Gate to Source Voltage        | VGS    | ±10         | V    |  |
|         | Drain current                 | ID     | -2.0        | Α    |  |
|         | Peak drain current            | IDp    | -8.0        | Α    |  |
|         | Channel temperature           | Tch    | 150         | °C   |  |
| SBD     | Reverse voltage               | VR     | 20          | V    |  |
|         | Forward current (Average)     | IF(AV) | 800         | mA   |  |
|         | Junction temperature          | Tj     | 125         | °C   |  |
| Overall | Operating ambient temperature | Topr   | -40 to +85  | °C   |  |
|         | Storage temperature           | Tstg   | -55 to +125 | °C   |  |
|         | Total power dissipation *1    | PD     | 540         | mW   |  |

Note: \*1 Measuring on ceramic substrate at 40 mm × 38 mm × 0.2 mm
PD absolute maximum rating without a heat shink: 150 mW





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■ Electrical Characteristics Ta = 25 °C ± 3 °C FET (P-ch.)

| Parameter  | Symbol   | Conditions                          | Min  | Тур   | Max  | Unit |
|--|----------|-------------------------------------|------|-------|------|------|
| Drain-source surrender voltage                   | VDSS     | ID = -1.0 mA, VGS = 0               | -20  |       |      | V    |
| Drain-source cutoff current                      | IDSS     | VDS = -20 V, VGS = 0                |      |       | -1.0 | μA   |
| Gate-source cutoff current                       | IGSS     | $VGS = \pm 8 \text{ V, VDS} = 0$    |      |       | ±10  | μA   |
| Gate threshold voltage                           | VTH      | ID = -1.0 mA, VDS = -10 V           | -0.4 | -0.75 | -1.1 | V    |
|  | RDS(on)1 | ID = -1.0 A, VGS = -4.0 V           |      | 80    | 120  |      |
| Drain-source ON resistance *1                    | RDS(on)2 | ID = -1.0 A, VGS = -2.5 V           |      | 100   | 170  | mΩ   |
|  | RDS(on)3 | ID = -0.5 A, VGS = -1.8 V           |      | 140   | 230  |      |
| Forward transfer admittance *1                   | Yfs      | ID = -1.0 A, VDS = -10 V, f = 1 kHz | 3.0  |       |      | S    |
| Short-circuit input capacitance (Common source)  | Ciss     |                                     |      | 300   |      | pF   |
| Short-circuit output capacitance (Common source) | Coss     | VDS = -10 V, VGS = 0, f = 1 MHz     |      | 30    |      |      |
| Reverse transfer capacitance (Common source)     | Crss     |                                     |      | 35    |      |      |
| Turn-on delay time *2                            | td(on)   | VDD = -10 V, VGS = 0 V to - 4 V     |      | 6     |      | ns   |
| Rise time *2                                     | tr       | ID = -1.0 A                         |      | 8     |      |      |
| Turn-off delay time *2                           | td(off)  | VDD = -10 V, VGS = -4 V to 0 V      |      | 57    |      | ns   |
| Fall time *2                                     | tf       | ID = -1.0 A                         |      | 55    |      | 115  |

1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors. Note:

#### **SBD**

| Parameter       | Symbol | Conditions  | Min | Тур | Max  | Unit |
|-----------------|--------|-------------|-----|-----|------|------|
| Forward voltage | VF     | IF = 800 mA |     |     | 0.47 | V    |
| Reverse current | IR     | VR = 20 V   |     |     | 80   | μA   |

Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7031 Measuring methods for diodes.

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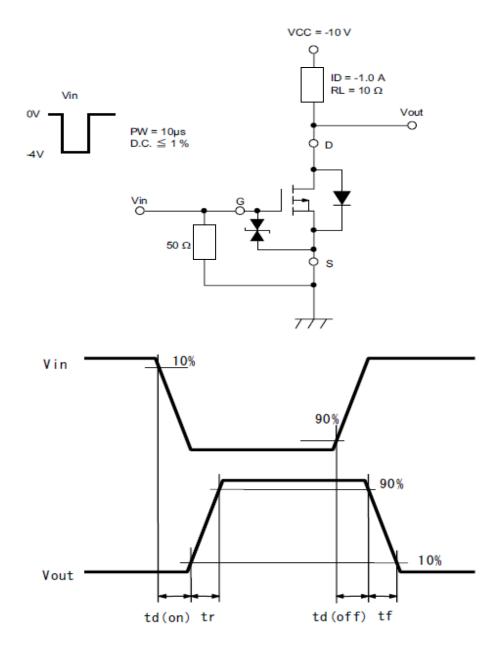
<sup>2. \*1</sup> Pulse measurement

<sup>\*2</sup> Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time

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\*2 Measurement circuit for Turn-on Delay Time/Rise Time/Turn-off Delay Time/Fall Time



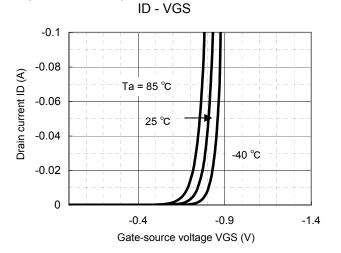
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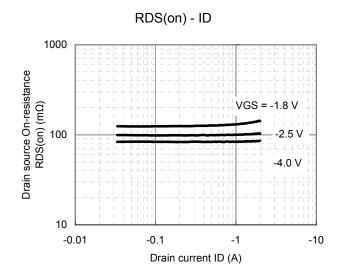
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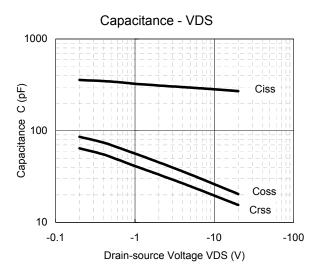
## Technical Data (reference)

ID - VDS -2 -4.0 V -1.8 -1.6 Drain current ID (A) -1.4 -1.2 -1 -0.8 -0.6 -0.4 VGS= -1.0 V -0.2 0 0 -0.2 -0.4 -0.6 Drain-source voltage VDS (V)



VDS - VGS -1.8 -1.6 Drain-source voltage VDS (V) -1.4 -1.2 -1 ID=-2 mA-0.8 -1 mA -0.6 -0.4 -0.5 mA -0.2 0 -2 0 -4 -6





Gate-source voltage VGS (V)

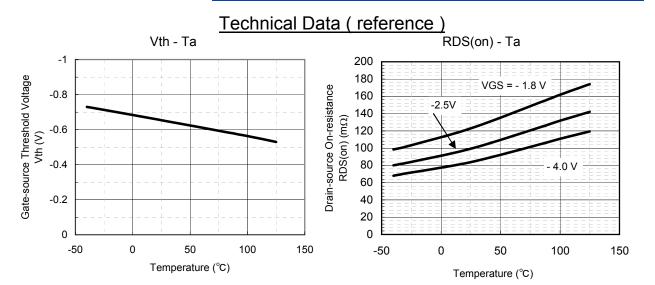
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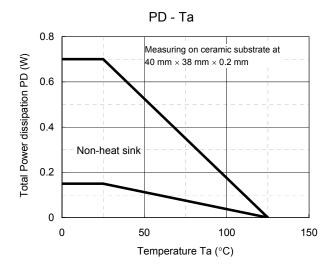
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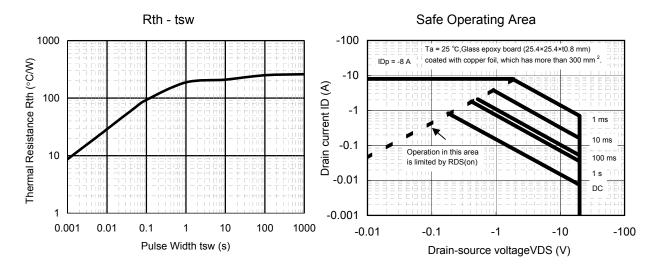
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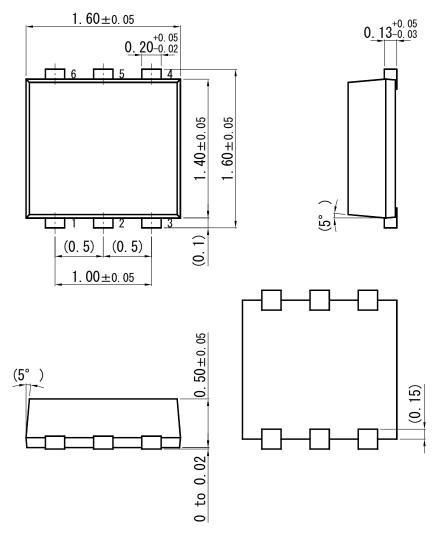
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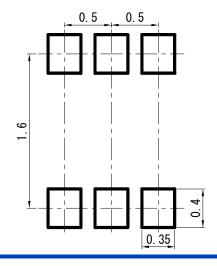
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## WSSMini6-F1

Unit: mm



#### ■ Land Pattern (Reference) (Unit: mm)



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